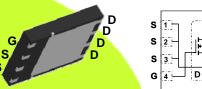


Features

- Optimized for 5V gate drive
- Ultra Low Qg & Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant



QFN 5mm x 6mm Plastic Package



Top View

Product Summary

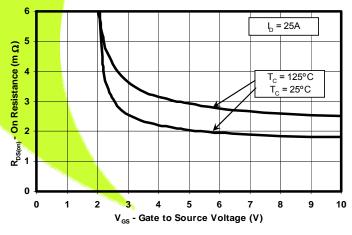
V_{DS}	25	V	
Q_g	14	nC	
Q_{gd}	2.5	nC	
$R_{ extsf{DS(on)}}$	$V_{GS} = 3.0V$	2.8	mΩ
	$V_{GS} = 4.5V$	2.1	mΩ
	$V_{GS} = 8.0V$	1.9	mΩ
V_{th}	1.1		V

Maximum Values (T_A = 25°C unless otherwise stated)

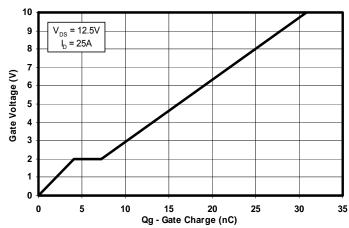
Symbol	Parameter	Value	Units
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+10 / -6	٧
l _D	Continuous Drain Current, T _C = 25°C	100	Α
	Continuous Drain Current ¹	31	Α
I _{DM}	Pulsed Drain Current, T _A = 25°C ²	200	Α
P _D	Power Dissipation ¹	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
Eas	Avalanche Energy, single pulse I_D =66A, L = 0.1mH, R_G = 25 Ω	218	mJ

- 1. R_{eJA} = 39°C/W on 1in² Cu (2 oz.) on 0.060" thick FR4 PCB.
- 2. See Figure 10





Gate Charge



Ordering Information

Туре	Package	Package Media	Qty	Ship
CSD16321Q5	QFN 5X6 Plastic Package	13 inch reel	2500	Tape and Reel



Electrical Characteristics (T_A = 25°C unless otherwise stated)

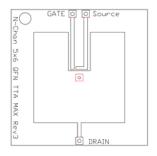
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Static Characteristics							
BV _{DSS}	Drain to Source Voltage	V _{GS} = 0V, I _D = 250µA	25	—	_	V	
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 20V	1 –	_	1	μΑ	
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = 10V	1 –	_	100	nA	
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.9	1.1	1.4	V	
		$V_{GS} = 3.0V, I_D = 25A$	_	2.8	3.5	mΩ	
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V, I _D = 25A	_	2.1	2.6	mΩ	
		V _{GS} = 8.0V, I _D = 25A	_	1.9	2.4	mΩ	
g fs	Transconductance	V _{DS} = 12.5V, I _D = 25A	_	150	_	S	
Dynamic	Characteristics						
Ciss	Input Capacitance		_	2360	3100	pF	
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V$	_	1700	2200	pF	
C _{RSS}	Reverse Transfer Capacitance	f = 1MHz	_	115	150	pF	
Rg	Series Gate Resistance		—	1.2	_	Ω	
Qg	Gate Charge Total (4.5V)		_	14	19	nC	
Q_{gd}	Gate Charge Gate to Drain	\\ -40.5\\ -05A	_	2.5	_	nC	
Q _{gs}	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_D = 25A$	_	4.0	_	nC	
Q _{g(th)}	Gate Charge at Vth]	_	2.1	_	nC	
Qoss	Output Charge	V _{DS} = 15V, V _{GS} = 0V	—	36	_	nC	
t _{d(on)}	Turn On Delay Time		—	11	_	ns	
tr	Rise Time	V _{DS} = 12.5V	_	19	_	ns	
t _{d(off)}	Turn Off Delay Time	$V_{GS} = 4.5 V I_{D} = 25 A$ $R_{G} = 2.7 \Omega$	_	40	_	ns	
t _f	Fall Time	NG - 2.7 S2	_	30	_	ns	
Diode Characteristics							
V _{SD}	Diode Forward Voltage	I _S = 25A, V _{GS} = 0V	T —	0.8	1.0	V	
Q _{rr}	Reverse Recovery Charge	V _{dd} =13V, I _F = 25A, di/dt = 300A/μs	_	33	_	nC	
t _{rr}	Reverse Recovery Time	V _{dd} =13V, I _F = 25A, di/dt = 300A/µs	_	32	_	ns	



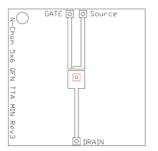
Thermal Characteristics (T_A = 25°C unless otherwise stated)

Symbol	Parameter		Тур	Max	Units
Thermal Characteristics					
R _θ JC	Thermal Resistance Junction to Case ³		1	1.1	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ^{3,4}		_	50	°C/W

- 3. $R_{\theta jc}$ is determined with the device mounted on a 1in square 2 oz. Cu pad on a 1.5x1.5 in .060in thick FR4 board. $R_{\theta jc}$ is guaranteed by design while $R_{\theta ca}$ is determined by the user's board design.
- 4. Device mounted on FR4 Material with 1in² of 2 oz. Cu.



Max Reja = 48° C/W when mounted on 1in² of 2 oz. Cu.



Max R_{θ}ja = 115°C/W when mounted on min pad area of 2 oz. Cu.

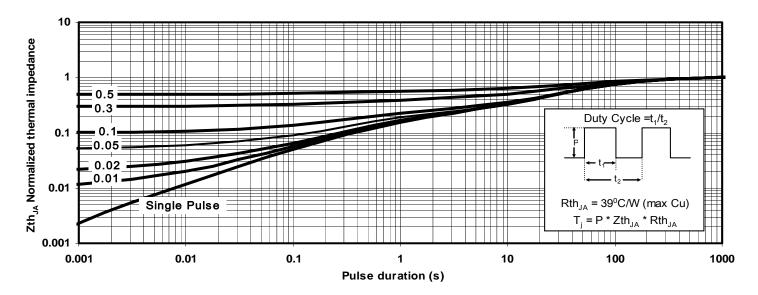
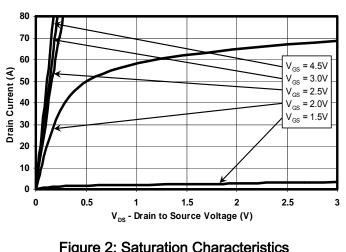


Figure 1: Transient Thermal Impedance



Typical MOSFET Characteristics (T_A = 25°C unless otherwise stated)



 $V_{DS} = 5V$ 70 60 Drain Current (A) 50 40 T_C = -55°C 30 $T_C = 25^{\circ}C$ 20 T_C = 125°C 10 0 2.5 V_{GS} - Gate to Source Voltage (V)

Figure 2: Saturation Characteristics

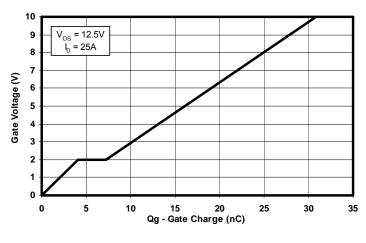


Figure 3: Transfer Characteristics

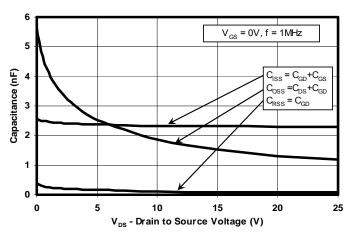


Figure 4: Gate Charge

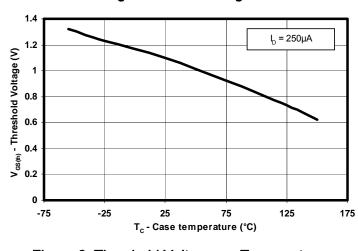


Figure 5: Capacitance

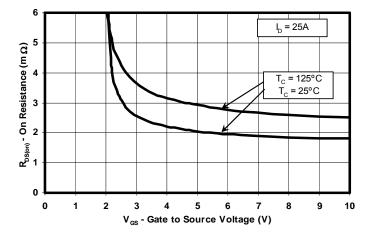
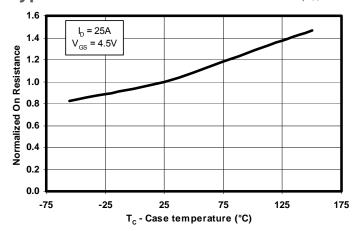


Figure 6: Threshold Voltage vs. Temperature

Figure 7: On Resistance vs. Gate Voltage



Typical MOSFET Characteristics (T_A = 25°C unless otherwise stated)



100
T_C = 125°C
T_C = 25°C
T_C = 25°C

0.001
0 0.2 0.4 0.6 0.8

V_{SD} - Source to Drain Voltage (V)

Figure 8: On Resistance vs. Temperature

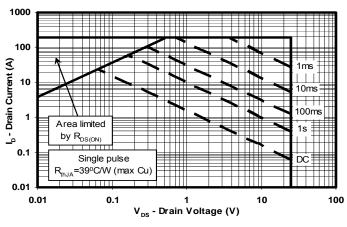


Figure 9: Typical Diode Forward Voltage

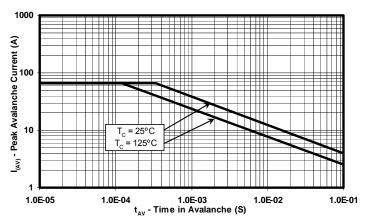
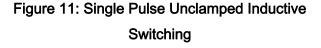


Figure 10: Maximum Safe Operating Area



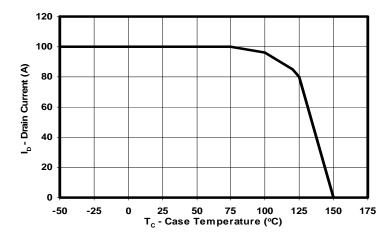
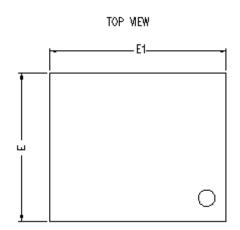
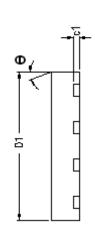


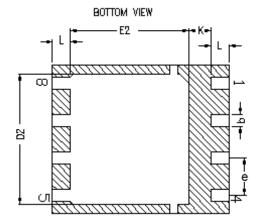
Figure 12: Maximum Drain Current vs. Temperature

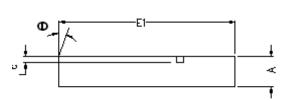


Q5 Package Dimensions









SIDE MEW

DIM	MILLIMETERS		INCHES		
DIIVI	Min	Max	Min	Max	
Α	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
С	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	4.320	4.520	0.170	0.178	
Е	4.900	5.100	0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	TYP	0.050		
L	0.510	0.710	0.020	0.028	
θ	0.00	-	-	1	
K	0.760	-	0.030	1	
F1	6.205	6.305	0.244	0.248	
F2	4.460	4.560	0.176	0.180	
F3	4.460	4.560	0.176	0.180	
F4	0.650	0.700	0.026	0.028	
F5	0.620	0.670	0.024	0.026	
F6	0.630	0.680	0.025	0.027	
F7	0.700	0.800	0.028	0.031	
F8	0.650	0.700	0.026	0.028	

0.670

5.000

4.560

F9

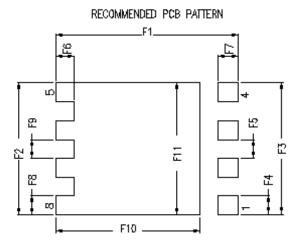
F10

F11

0.620

4.900

4.460



0.024

0.193

0.176

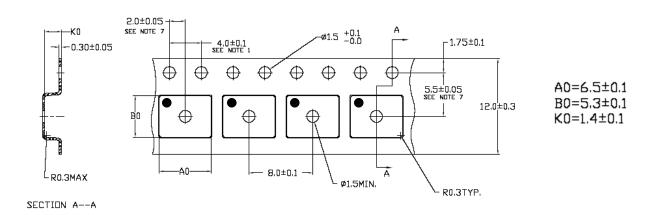
0.026

0.197

0.180



Q5 Tape and Reel Information



Note:

- 1. 10 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE +/-0.2
- CAMBER NOT TO EXCEED 1mm IN 100mm, NONCUMULATIVE OVER 250mm
- 3. MATERIAL:BLACK STATIC DISSIPATIVE POLYSTYRENE
- 4. ALL DIMENSIONS ARE IN mm (UNLESS OTHERWISE SPECIFIED)
- 5. THICKNESS: 0.30 +/-0.05mm

Package Marking Information

Location:

1st Line

CSD = Fixed Characters

NNNNN = Product Code

2nd Line (Date Code)

YY = Last 2 digits of the Year

WW = 2-digit Work Week

C = Country of Origin

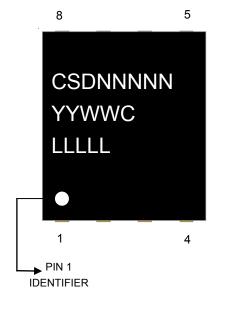
> Philippines = P

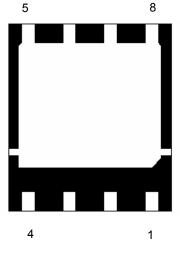
> Taiwan = T

> China = C

3rd Line

LLLLL= Last 5 digits of the Wafer Lot #







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